

# DATA SHEET

## BAV101~BAV103

### HIGH VOLTAGE SURFACE MOUNT SWITCHING DIODES

**VOLTAGE** 120 to 250 Volts **POWER** 300 mWatts **MINI-MELF/LL-34** Unit : inch (mm)

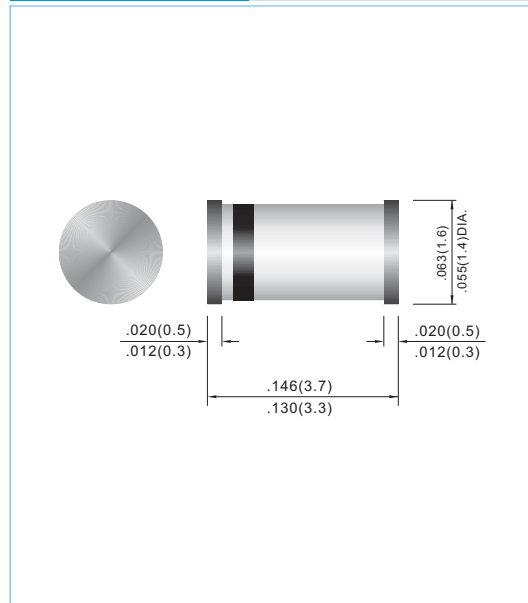
#### FEATURES

- Fast switching Speed.
- Surface Mount Package Ideally Suited For Automatic Insertion.
- Silicon Epitaxial Planar Construction.
- Both normal and Pb free product are available :  
Normal : 80~95% Sn, 5~20% Pb  
Pb free: 98.5% Sn above

#### MECHANICAL DATA

- Case: Mini Melf, Glass
- Terminals: Solderable per MIL-STD-202E, Method 208
- Polarity: Cathode Band
- Marking: Cathode Band Only
- Weight: 0.03 grams
- Packing information

T/R - 2.5K per 7" plastic Reel



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	BAV101	BAV102	BAV103	UNITS
Reverse Voltage	V <sub>R</sub>	100	150	200	V
Peak Reverse Voltage	V <sub>RM</sub>	120	200	250	V
Rectified Current (Average), Half Wave Rectification with Resistive Load and f >= 50 Hz	I <sub>D</sub>		200		mA
Peak Forward Surge Current, t=1.0s	I <sub>FSM</sub>		1.0		A
Power Dissipation Derate Above at 25°C	P <sub>D</sub>		300		mW
Maximum Forward Voltage, I <sub>F</sub> = 100mA	V <sub>F</sub>		1.0		V
Maximum DC Reverse Current at Rated DC Blocking Voltage T <sub>J</sub> = 25°C	I <sub>R</sub>		0.1		uA
Typical Junction Capacitance (Note 1)	C <sub>J</sub>		0.95		pF
Maximum Reverse Recovery (Note 2)	T <sub>RR</sub>		75		ns
Maximum Thermal Resistance	R <sub>θJA</sub>		350		°C / W
Operation Junction Storage Temperature Range	T <sub>STG</sub>		-65 TO +175		°C

#### NOTE:

1. C<sub>J</sub> at V<sub>R</sub>=0, f=1MHZ
2. From I<sub>F</sub>=10mA to I<sub>R</sub>=-1mA, V<sub>R</sub>=6Volts, R<sub>L</sub>=100Ω

**RATING AND CHARACTERISTIC CURVES**

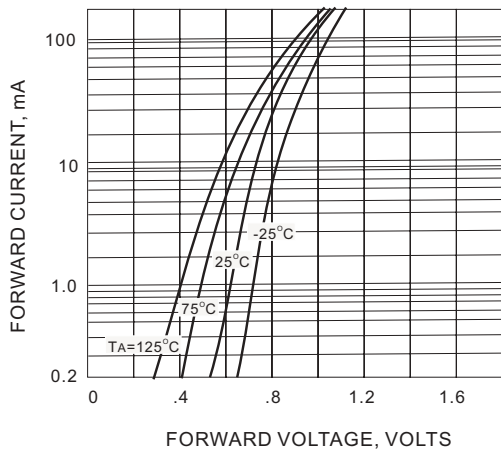


Fig.1 FORWARD CHARACTERISTICS

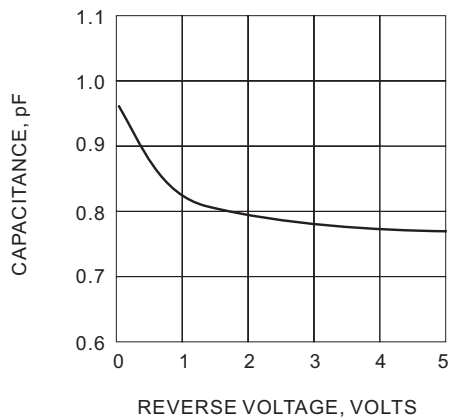


Fig.2 TYPICAL CAPACITANCE vs REVERSE VOLTAGE

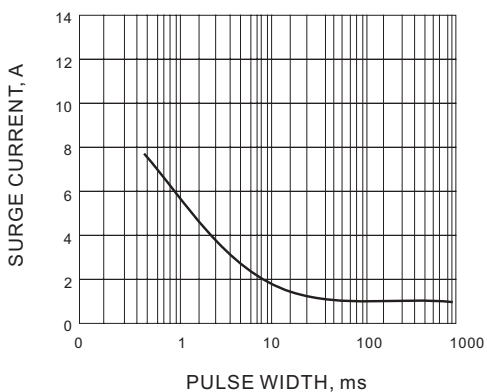


Fig.3 SURGE CURRENT CHARACTERISTIC

单击下面可查看定价，库存，交付和生命周期等信息

[>>Panjit\(强茂\)](#)